

NTE595 Silicon Diode, Dual, Common Cathode, High Speed

Description:

The NTE595 consists of two silicon diodes in an SOT-23 type surface mount package. The cathodes are common and the device is intended for high-speed switching applications in thick and thin-film circuits.

Absolute Maximum Ratings:

Continuous Reverse Voltage, V_R	70V
Repetitive Peak Reverse Voltage, V_{RRM}	70V
Non-Repetitive Peak Forward Current (Per device, $t = 1s$), I_{FSM}	500mA
Average Rectified Forward Current (Average over any 20ms period, Note 1), $I_{F(AV)}$	250mA
DC Forward Current, I_F	250mA
Repetitive Peak Forward Current, I_{FRM}	250mA
Total Power Dissipation ($T_A \leq +25^\circ C$), P_{tot}	200mW
Operating Junction Temperature, T_J	+175°C
Storage Temperature Range, T_{stg}	-65° to +175°C
Thermal Resistance, Junction-to-Ambient (Note 2), R_{thJA}	430K/W

Note 1. Measured under pulse conditions: $t_p \leq 0.5ms$, $I_{F(AV)} = 150mA$, $t_{(av)} \leq 1ms$, for sinusoidal operation.

Note 2. Mounted on a ceramic substrate of .314 (8mm) x .393 (10mm) x .027 (0.7mm).

Electrical Characteristics (Per Diode): ($T_J = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F = 1mA$	—	—	715	mV
		$I_F = 10mA$	—	—	855	mV
		$I_F = 50mA$	—	—	1000	mV
		$I_F = 150mA$	—	—	1250	mV
Reverse Current	I_R	$V_R = 70V$	—	—	5	μA
		$V_R = 70V$, $T_J = +150^\circ C$	—	—	100	μA
Diode Capacitance	C_d	$V_R = 0$, $f = 1MHz$	—	—	1.5	pF
Forward Recovery Voltage (When switched to $I_F = 10mA$)	V_{fr}	$t_r = 20ns$	—	—	1.75	V

Electrical Characteristics (Per Diode): ($T_J = +25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Recovery Time (When switched from $I_F = 10\text{mA}$ to $I_R = 10\text{mA}$)	t_{rr}	measured at $I_R = 1\text{mA}$, $R_L = 100\Omega$	–	–	6	ns
Recovery Charge (When switched from $I_F = 10\text{mA}$ to $V_R = 5\text{V}$)	Q_s	$R_L = 100\Omega$	–	–	45	pC

